- Wide Range of Supply Voltages, Single or Dual Supplies
- Wide Bandwidth

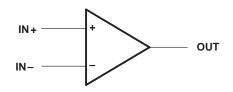
description

- Large Output Voltage Swing
- Output Short-Circuit Protection
- Internal Frequency Compensation
- Low Input Bias Current
- Designed to Be Interchangeable With National Semiconductor LM2900 and LM3900, Respectively

#### **N PACKAGE** (TOP VIEW) 1IN+ V<sub>CC</sub> 14 2IN+**∏** 2 13 3IN+ 2IN-[] 3 12 4IN+ 20UT 4 4IN-11 10UT 140UT 5 10 1IN-3OUT 6 9 GND 3IN-7 8

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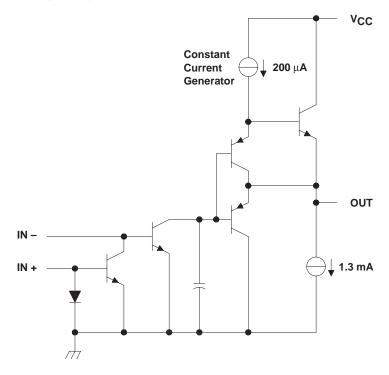
#### symbol (each amplifier)



These devices consist of four independent, highgain frequency-compensated Norton operational amplifiers that were designed specifically to operate from a single supply over a wide range of voltages. Operation from split supplies is also possible. The low supply current drain is essentially independent of the magnitude of the supply voltage. These devices provide wide bandwidth and large output voltage swing.

The LM2900 is characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C, and the LM3900 is characterized for operation from  $0^{\circ}$ C to  $70^{\circ}$ C.

#### schematic (each amplifier)



PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

	LM2900	LM3900	UNIT	
Supply voltage, V <sub>CC</sub> (see Note 1)	36	36	V	
Input current	20 20 n			
Duration of output short circuit (one amplifier) to ground at (or below) 25°C free-air temperature (see Note 2)	unlimited	unlimited		
Continuous total dissipation	See Dissipation Rating Table			
Operating free-air temperature range	-40 to 85	0 to 70	°C	
Storage temperature range	-65 to 150	-65 to 150	°C	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260	260	°C	

NOTES: 1. All voltage values, except differential voltages, are with respect to the network ground terminal.

2. Short circuits from outputs to  $V_{CC}$  can cause excessive heating and eventual destruction.

	DISSIPATION RATING TABLE								
$\begin{array}{c} T_{A} \leq 25^\circ C \\ POWER RATING \end{array}$		<b>A</b>	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING				
	N	1150 mW	9.2 mW/°C	736 mW	598 mW				

#### recommended operating conditions

	LM2	900	LM3900		UNIT	
	MIN	MAX	MIN	MAX	UNIT	
Supply voltage, V <sub>CC</sub> (single supply)	4.5	32	4.5	32	V	
Supply voltage, V <sub>CC+</sub> (dual supply)	2.2	16	2.2	16	V	
Supply voltage, V <sub>CC</sub> (dual supply)	-2.2	-16	-2.2	-16	V	
Input current (see Note 3)		-1		-1	mA	
Operating free-air temperature, T <sub>A</sub>	-40	85	0	70	°C	

NOTE 3: Clamp transistors are included that prevent the input voltages from swinging below ground more than approximately -0.3 V. The negative input currents that may result from large signal overdrive with capacitive input coupling must be limited externally to values of approximately -1 mA. Negative input currents in excess of -4 mA causes the output voltage to drop to a low voltage. These values apply for any one of the input terminals. If more than one of the input terminals are simultaneously driven negative, maximum currents are reduced. Common-mode current biasing can be used to prevent negative input voltages.



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		t		LM2900			LM3900			
PARAMETER		TEST CONDITIONS <sup>†</sup>		MIN TYP		MAX	MIN	TYP	MAX	UNIT
lun	Input bias current (inverting input)	O	T <sub>A</sub> = 25°C		30	200		30	200	nA
IВ		$  _{+} = 0$	T <sub>A</sub> = Full range		300			300		ΠA
	Mirror gain	$I_{I+} = 20 \ \mu A$ to 200 $\mu A$ T <sub>A</sub> = Full range,		0.9		1.1	0.9		1.1	μΑ/μΑ
	Change in mirror gain	See Note 4			2%	5%		2%	5%	
	Mirror current	V <sub>I +</sub> = V <sub>I</sub> , See Note 4	$T_A = Full range,$		10	500		10	500	μΑ
A <sub>VD</sub>	Large-signal differential voltage amplification	V <sub>O</sub> = 10 V, f = 100 Hz	R <sub>L</sub> = 10 kΩ,	1.2	2.8		1.2	2.8		V/mV
r <sub>i</sub>	Input resistance (inverting input)				1			1		MΩ
r <sub>o</sub>	Output resistance				8			8		kΩ
B <sub>1</sub>	Unity-gain bandwidth (inverting input)				2.5			2.5		MHz
<sup>k</sup> SVR	Supply voltage rejection ratio $(\Delta V_{CC} / \Delta V_{IO})$				70			70		dB
			$R_L = 2 k\Omega$	13.5			13.5			
Vон	High-level output voltage	$ I_{ +} = 0,$ $ I_{ -} = 0$	V <sub>CC</sub> = 30 V, No load		29.5			29.5		V
VOL	Low-level output voltage	$I_{ +} = 0,$ $R_{L} = 2 k\Omega$	I <sub>I —</sub> = 10 μA,		0.09	0.2		0.09	0.2	V
los	Short-circuit output current (output internally high)	$I_{I+} = 0, V_O = 0$	I <sub>I</sub> _= 0,	-6	-18		-6	-10		mA
	Pulldown current			0.5	1.3		0.5	1.3		mA
IOL	Low-level output current <sup>‡</sup>	I <sub>I –</sub> = 5 μA	$V_{OL} = 1 V$		5			5		mA
ICC	Supply current (four amplifiers)	No load			6.2	10		6.2	10	mA

## electrical characteristics, $V_{CC}$ = 15 V, $T_A$ = 25°C (unless otherwise noted)

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified. Full range for T<sub>A</sub> is -40°C to 85°C for LM2900 and 0°C to 70°C for LM3900.

<sup>‡</sup> The output current-sink capability can be increased for large-signal conditions by overdriving the inverting input.

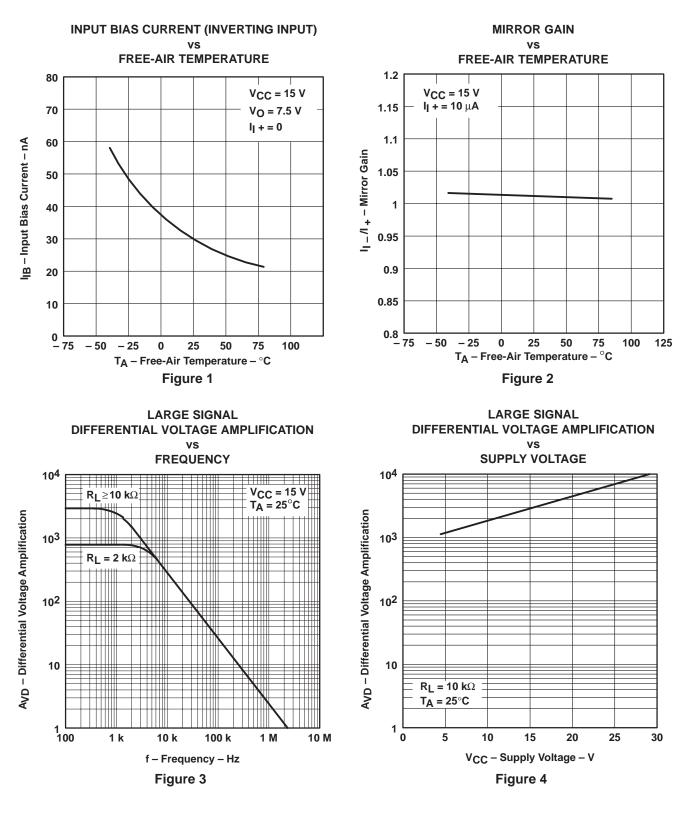
NOTE 4: These parameters are measured with the output balanced midway between V<sub>CC</sub> and GND.

# operating characteristics, V\_{CC\pm} = $\pm 15$ V, T\_A = 25°C

PARAMETER		TEST CONDITIONS				TYP	MAX	UNIT	
SR Slew rate at unity gain	Slow roto at upity goin	Low-to-high output	$V_{0} = 10 V_{.}$	C. 100 pE	$R_1 = 2 k\Omega$		0.5		V/µs
	High-to-low output	$V_{O} = 10 V_{,}$	C <sub>L</sub> = 100 pF,	KT = 5 K25		20		v/μs	



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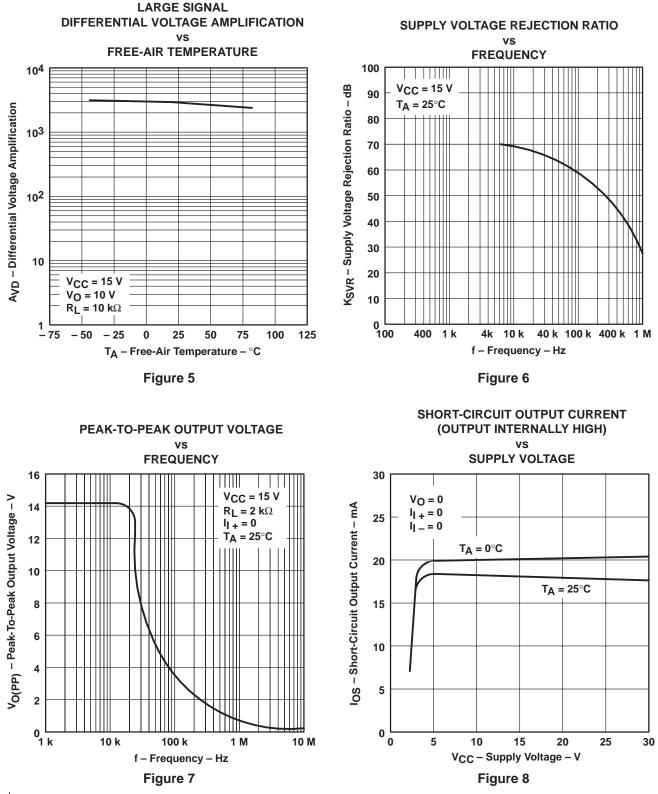
TYPICAL CHARACTERISTICS<sup>†</sup>

<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



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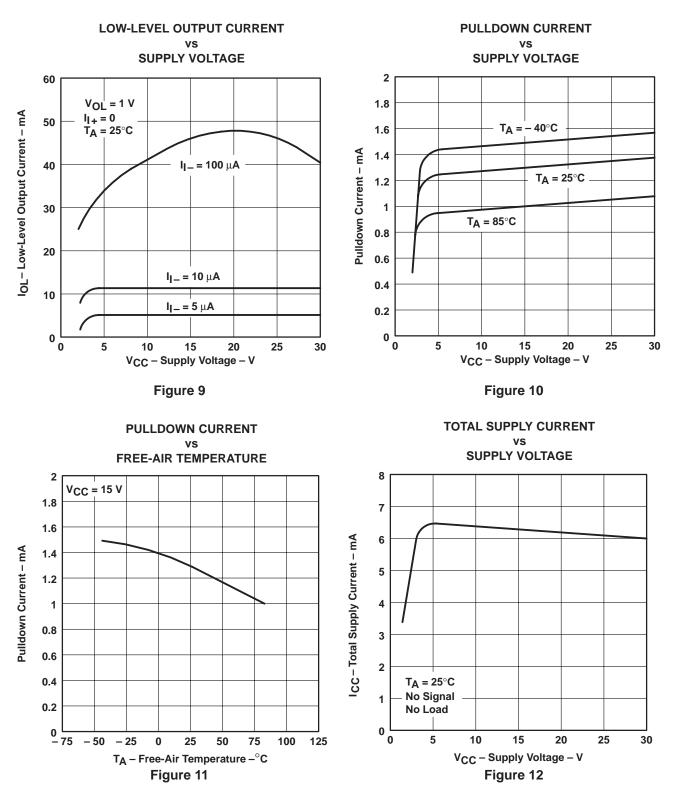
## **TYPICAL CHARACTERISTICS<sup>†</sup>**



<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



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## **TYPICAL CHARACTERISTICS<sup>†</sup>**

<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

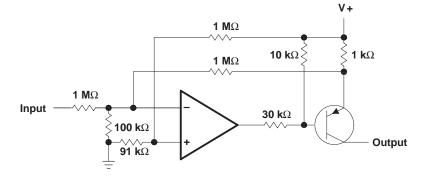


#### **APPLICATION INFORMATION**

Norton (or current-differencing) amplifiers can be used in most standard general-purpose operational amplifier applications. Performance as a dc amplifier in a single-power-supply mode is not as precise as a standard integrated-circuit operational amplifier operating from dual supplies. Operation of the amplifier can best be understood by noting that input currents are differenced at the inverting input terminal and this current then flows through the external feedback resistor to produce the output voltage. Common-mode current biasing is generally useful to allow operating with signal levels near (or even below) ground.

Internal transistors clamp negative input voltages at approximately -0.3 V but the magnitude of current flow has to be limited by the external input network. For operation at high temperature, this limit should be approximately  $-100 \,\mu$ A.

Noise immunity of a Norton amplifier is less than that of standard bipolar amplifiers. Circuit layout is more critical since coupling from the output to the noninverting input can cause oscillations. Care must also be exercised when driving either input from a low-impedance source. A limiting resistor should be placed in series with the input lead to limit the peak input current. Current up to 20 mA will not damage the device, but the current mirror on the noninverting input will saturate and cause a loss of mirror gain at higher current levels, especially at high operating temperatures.



 $I_{O} \approx 1 \text{ mA per input volt}$ 



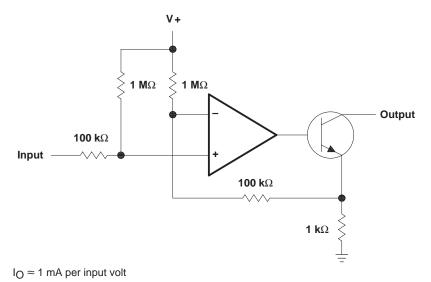


Figure 14. Voltage-Controlled Current Sink



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